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DUAL DIGIT LED DISPLAY (0.40 Inch)



Lead-Free Parts

LDD495/64-XX-PF

DATA SHEET

DOC. NO : QW0905-LDD495/64-XX-PF

REV. : A

DATE : 15 - Dec. - 2008



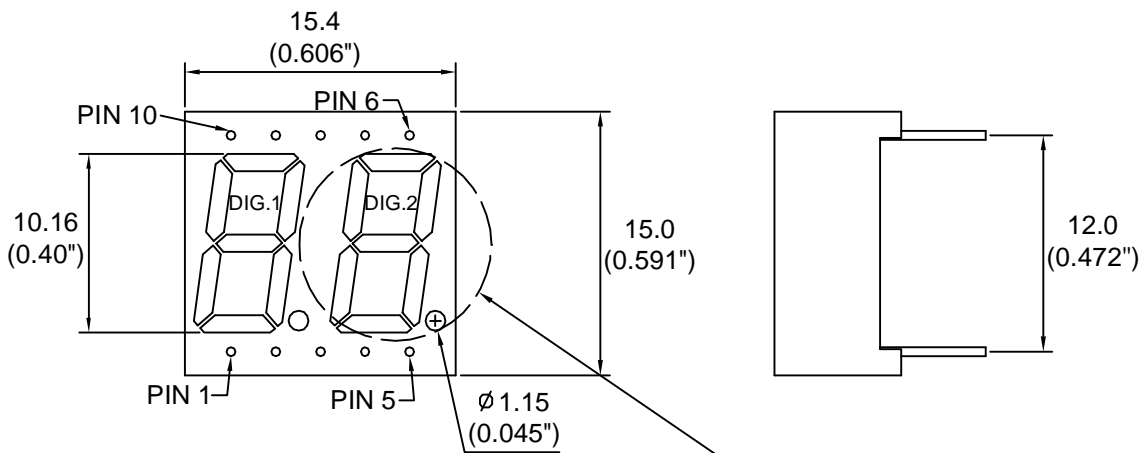
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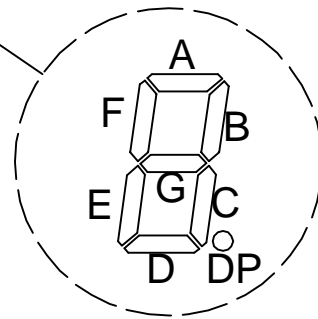
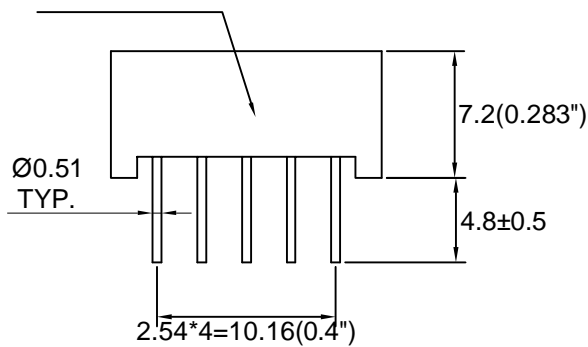
PART NO. LDD495/64-XX-PF

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Package Dimensions



LDD495/64-XX-PF
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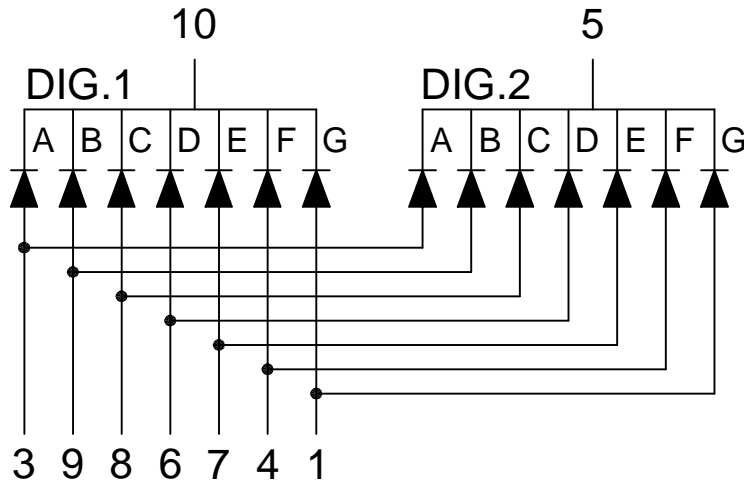
PIN NO.1 →

Note : 1.All dimension are in millimeters and (Inch) tolerance is $\pm 0.25\text{mm}$ unless otherwise noted.
2.Specifications are subject to change without notice.

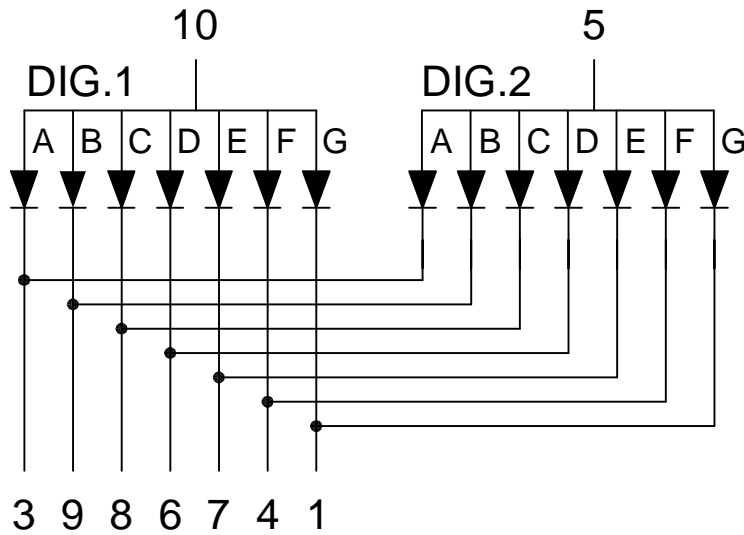


Internal Circuit Diagram

LDD4954-XX-PF



LDD4964-XX-PF



PIN 2:No Pin



Electrical Connection

PIN NO.	LDD4954-XX-PF	PIN NO.	LDD4964-XX-PF
1	Anode G	1	Cathode G
2	No Pin	2	No Pin
3	Anode A	3	Cathode A
4	Anode F	4	Cathode F
5	Common Cathode Dig.2	5	Common Anode Dig.2
6	Anode D	6	Cathode D
7	Anode E	7	Cathode E
8	Anode C	8	Cathode C
9	Anode B	9	Cathode B
10	Common Cathode Dig.1	10	Common Anode Dig.1



Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Ratings	UNIT
		E	
Forward Current Per Chip	IF	30	mA
Peak Forward Current Per Chip (Duty 1/10,0.1ms Pulse Width)	IFP	120	mA
Power Dissipation Per Chip	PD	100	mW
Reverse Current Per Any Chip	Ir	10	μA
Operating Temperature	Topr	-25 ~ +85	°C
Storage Temperature	Tstg	-25 ~ +85	°C

Part Selection And Application Information(Ratings at 25°C)

PART NO	CHIP		common cathode or anode	λ P (nm)	Δ λ (nm)	Electrical					IV-M
	Material	Emitted				Vf(v)			Iv(mcd)		
						Min.	Typ.	Max.	Min.	Typ.	
LDD4954-XX-PF	GaAsP/GaP	Orange	Common Cathode	635	45	1.7	2.1	2.6	1.35	2.35	2:1
LDD4964-XX-PF			Common Anode								

Note : 1. The forward voltage data did not including ±0.1V testing tolerance.
2. The luminous intensity data did not including ±15% testing tolerance.



Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Chip	Iv	mcd	If=10mA
Peak Wavelength	λP	nm	If=20mA
Spectral Line Half-Width	$\Delta \lambda$	nm	If=20mA
Reverse Current Any Chip	Ir	μA	Vr=5V
Luminous Intensity Matching Ratio	IV-M		



Typical Electro-Optical Characteristics Curve

E CHIP

Fig.1 Forward current vs. Forward Voltage

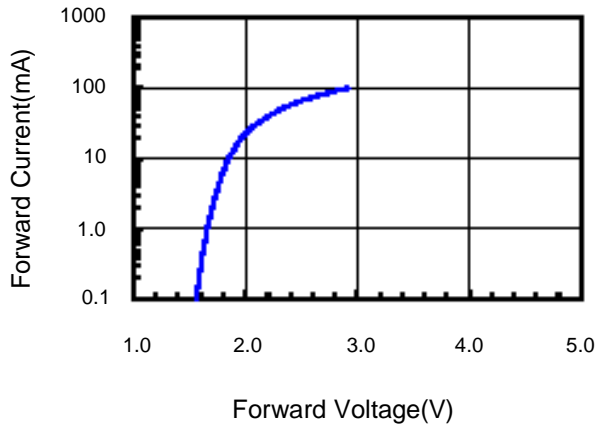


Fig.2 Relative Intensity vs. Forward Current

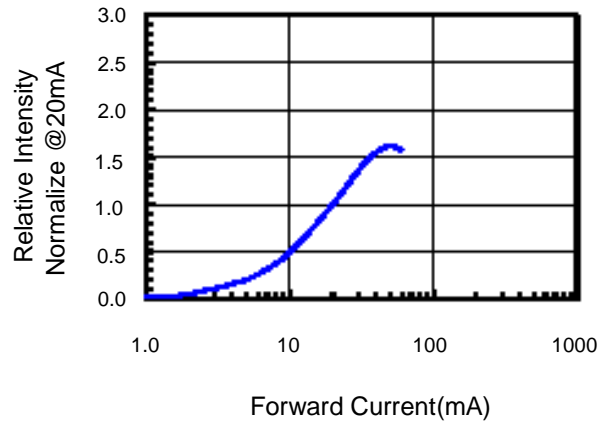


Fig.3 Forward Voltage vs. Temperature

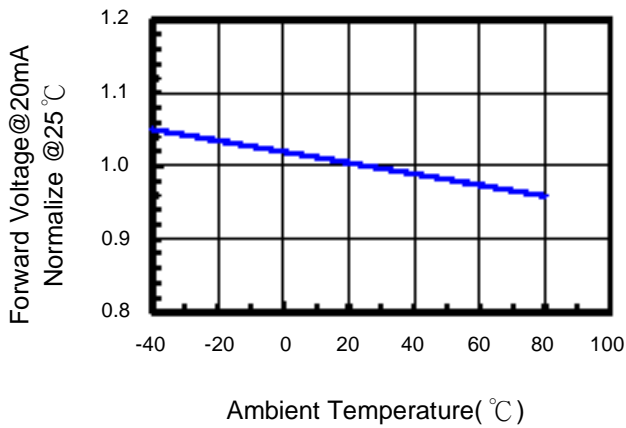


Fig.4 Relative Intensity vs. Temperature

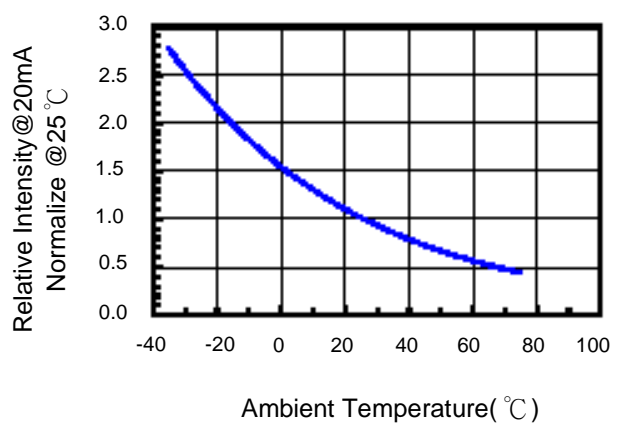
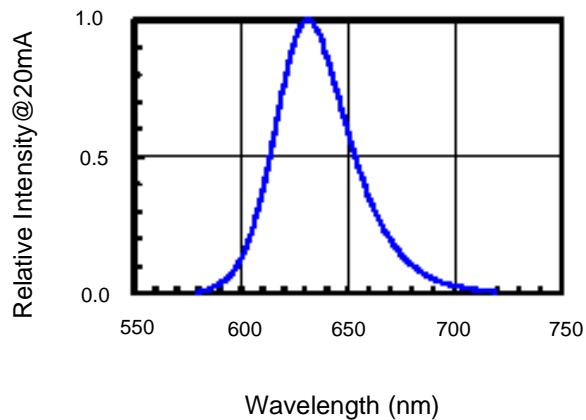


Fig.5 Relative Intensity vs. Wavelength





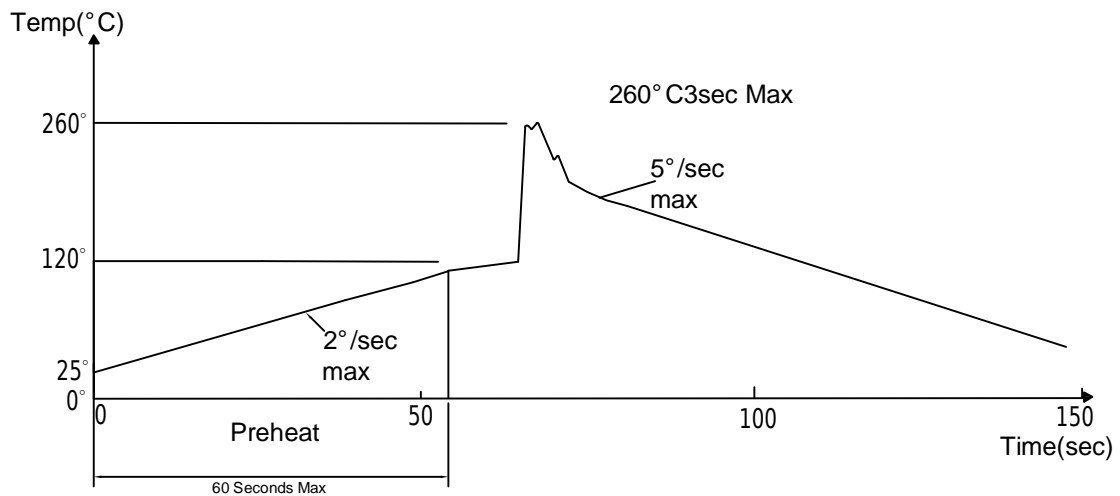
Soldering Condition(Pb-Free)

1.Iron:

Soldering Iron:30W Max
Temperature 350 ° C Max
Soldering Time:3 Seconds Max(One time only)
Distance:Solder Temperature 1/16 Inch Below Seating
Plane For 3 Seconds At 260 ° C

2.Wave Soldering Profile

Dip Soldering
Preheat: 120 ° C Max
Preheat time: 60seconds Max
Ramp-up
2° C/sec(max)
Ramp-Down:-5 ° C/sec(max)
Solder Bath:260 ° C Max
Dipping Time:3 seconds Max
Distance:Solder Temperature 1/16 Inch Below Seating
Plane For 3 Seconds At 260 ° C



Note: 1.Wave solder should not be made more than one time.
2.You can just only select one of the soldering conditions as above.

**Reliability Test:**

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=10mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of detemining the resistance of a part in electrical and themal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=105°C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40°C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65°C±5°C 2.RH=90%~95% 3.t=240hrs±2hrs	The purpose of this test is the resistance of the device under tropical for hours.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105°C±5°C & -40°C±5°C (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260°C±5°C 2.Dwell time= 10±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230°C±5°C 2.Dwell time=5±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2